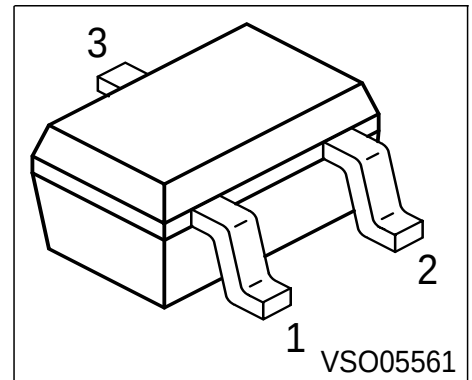
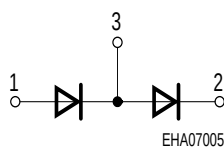


Silicon Schottky Diodes

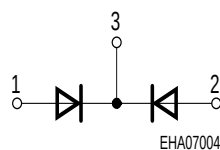
- For mixer applications in the VHF / UHF range
- For high-speed switching applications



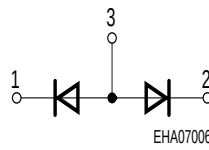
BAT17-04W



BAT17-05W



BAT17-06W



Type	Marking	Pin Configuration			Package
BAT17-04W	54s	1 = A1	2 = C2	3 = C1/A2	SOT323
BAT17-05W	55s	1 = A1	2 = A2	3 = C1/2	SOT323
BAT17-06W	56s	3 = C1	2 = C2	3 = A1/2	SOT323

Maximum Ratings

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	4	V
Forward current	I_F	130	mA
Total power dissipation, $T_S \leq 92\text{ °C}$	P_{tot}	150	mW
Junction temperature	T_j	150	°C
Operating temperature range	T_{op}	-55 ... 150	
Storage temperature	T_{stg}	-55 ... 150	

Thermal Resistance

Junction - soldering point ¹⁾	R_{thJS}	≤ 390	K/W
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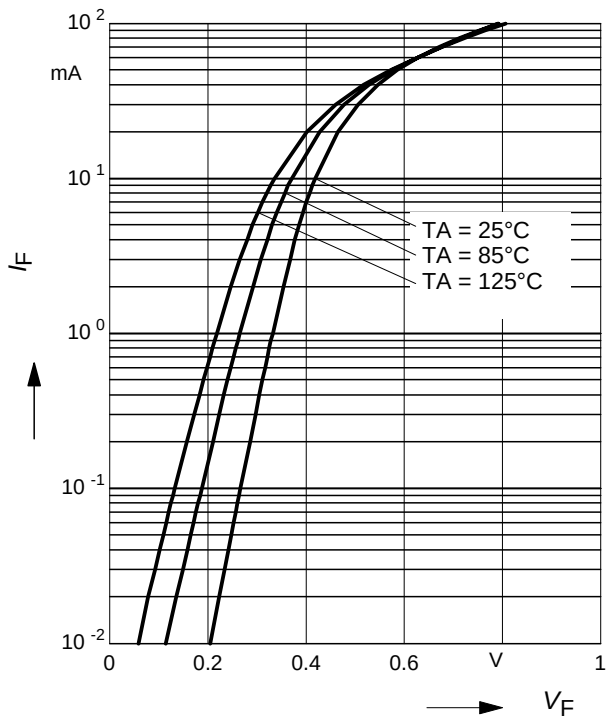
¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25\text{ °C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC characteristics					
Breakdown voltage $I_{(BR)} = 10\text{ }\mu\text{A}$	$V_{(BR)}$	4	-	-	V
Reverse current $V_R = 3\text{ V}$ $V_R = 4\text{ V}$	I_R	- -	- -	0.25 10	μA
Reverse current $V_R = 3\text{ V}, T_A = 60\text{ }^{\circ}\text{C}$	I_R	-	-	1.25	
Forward voltage $I_F = 0.1\text{ mA}$ $I_F = 1\text{ mA}$ $I_F = 10\text{ mA}$	V_F	200 250 350	275 340 425	350 450 600	mV
AC characteristics					
Diode capacitance $V_R = 0\text{ V}, f = 1\text{ MHz}$	C_T	0.4	0.55	0.75	pF
Differential forward resistance $I_F = 5\text{ mA}, f = 100\text{ kHz}$	r_f	-	8	15	Ω

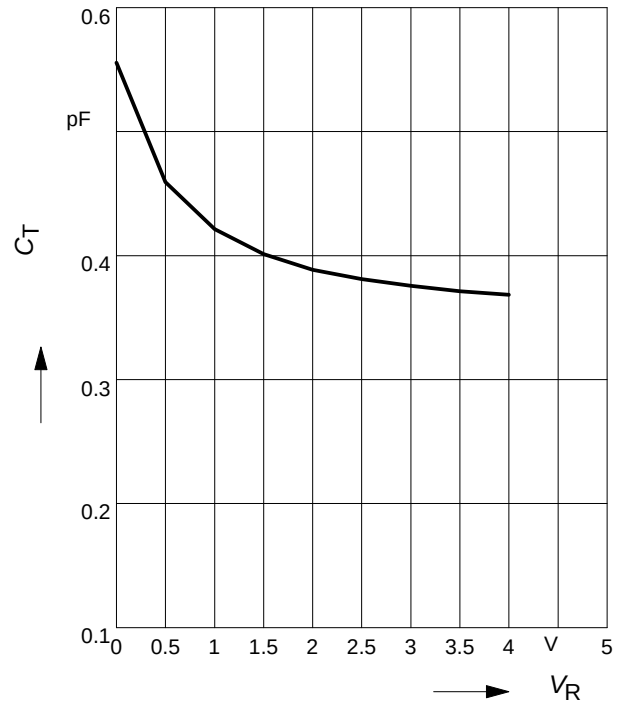
Forward current $I_F = f(V_F)$

T_A = parameter



Diode capacitance $C_T = f(V_R)$

$f = 1\text{MHz}$



Leakage current $I_R = f(V_R)$

T_A = Parameter

